



25V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary NPN Type: MMBT4124
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

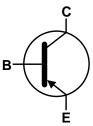
Mechanical Data

- Case: SOT23
- Case Material: Molded plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

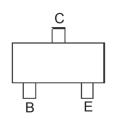








Device Symbol



Top View Pin-Out

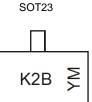
Ordering Information (Note 4)

Ī	Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ı	MMBT4126-7-F	Active	AEC-Q101	K2B	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K2B = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2016	20	017	2018	2	019	2020		2021	2022		2023
Code	D		E	F		G	Н		ı	J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-4.0	V
Collector Current	Ic	-200	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

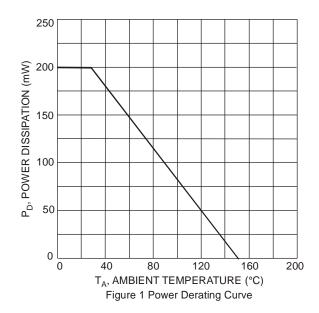
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information





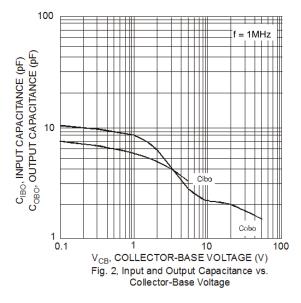
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-25	_	_	V	$I_C = -10\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 7)	BV _{CEO}	-25	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-4.0	_	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current	I _{CBO}	-	_	-50	nA	$V_{CB} = -20V, I_{E} = 0$
Collector Cut-Off Current	I _{EBO}	-	_	-50	nA	$V_{EB} = -3.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h _{FE}	120		360 —	_	$I_C = -2.0 \text{mA}, V_{CE} = -1.0 \text{V}$
Do ourient dann	"FE	60				$I_C = -50 \text{mA}, V_{CE} = -1.0 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE} (SAT)	_	_	-0.4	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-0.95	V	$I_C = -50 \text{mA}, I_B = 5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{OBO}	_	_	4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{IBO}	_	_	10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$
Small Signal Current Gain	h _{FE}	120	_	480	_	$V_{CE} = -1.0V$, $I_{C} = -2.0mA$, $f = 1.0kHz$
Current Gain Bandwidth Product	f _T	250			MHz	$V_{CE} = -20V, I_{C} = -10mA,$ f = 100MHz
Noise Figure	NF	_		4.0	dB	V_{CE} = -5.0V, I_{C} = -100 μ A, R_{S} = 1.0k Ω , f = 1.0kHz

Note: 7. Short duration pulse test used to minimize self-heating effect.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



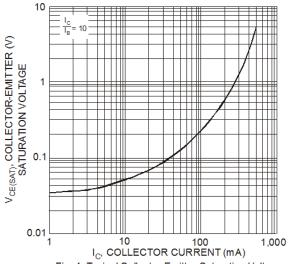
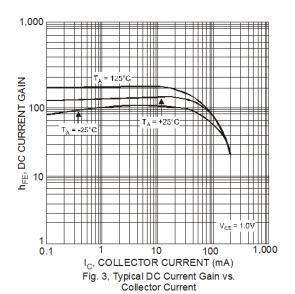


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



1.0

0.9

0.9

0.7

0.5

10

10

10

10

10

10

10

10

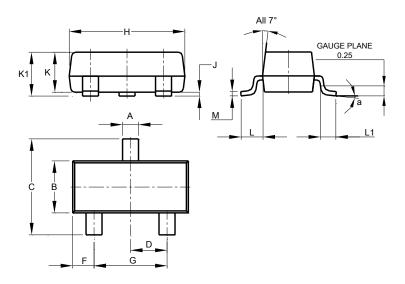
Fig. 5, Typical Base-Emitter
Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

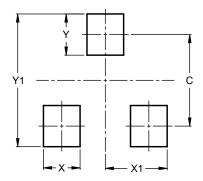


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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